

EECS 312 Discussion 7

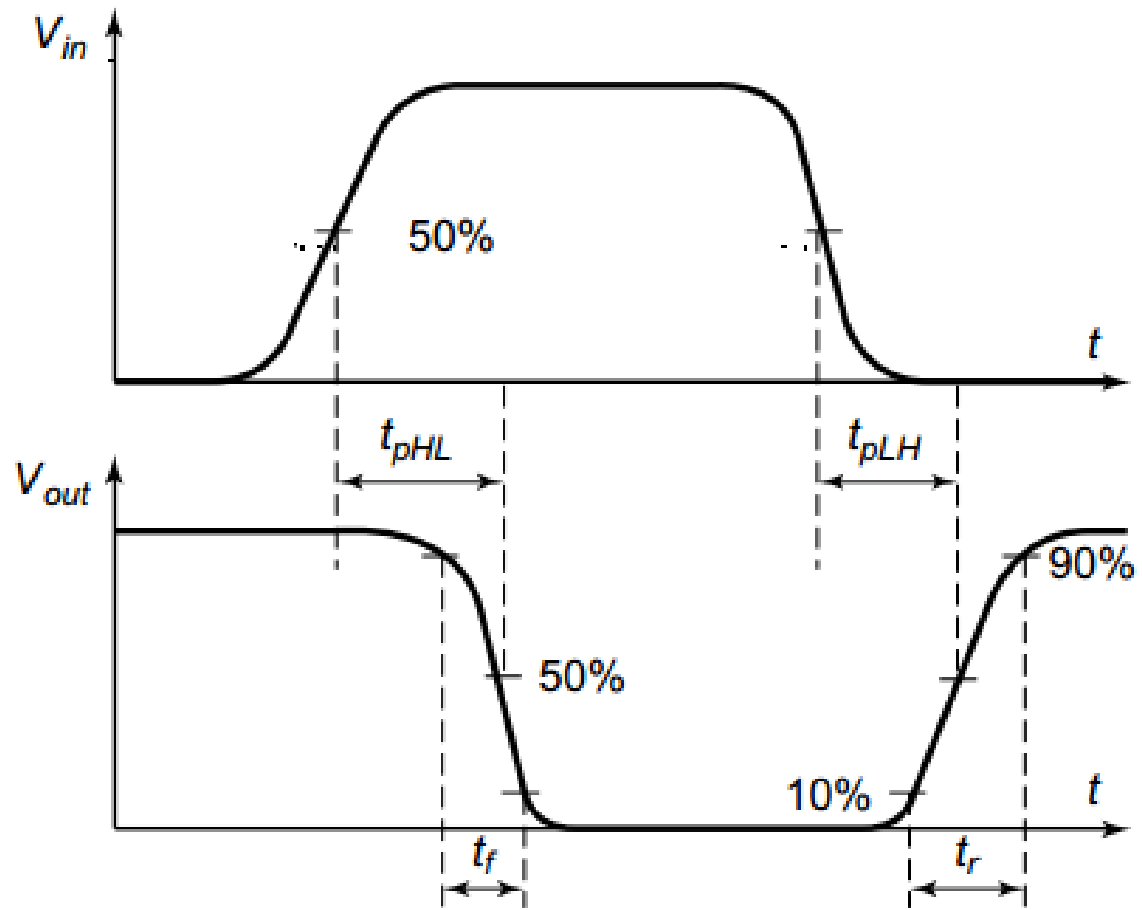
10/18

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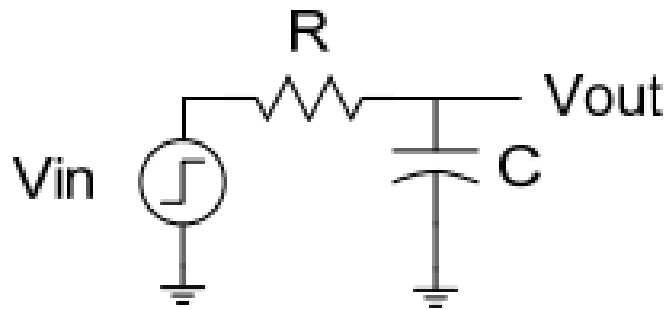
Overview

- Reminder
 - Lab 3: Due Oct 25
- Dis 6 review
- Logic effort
- Midterm review

Delay Definition



A First-Order RC Network

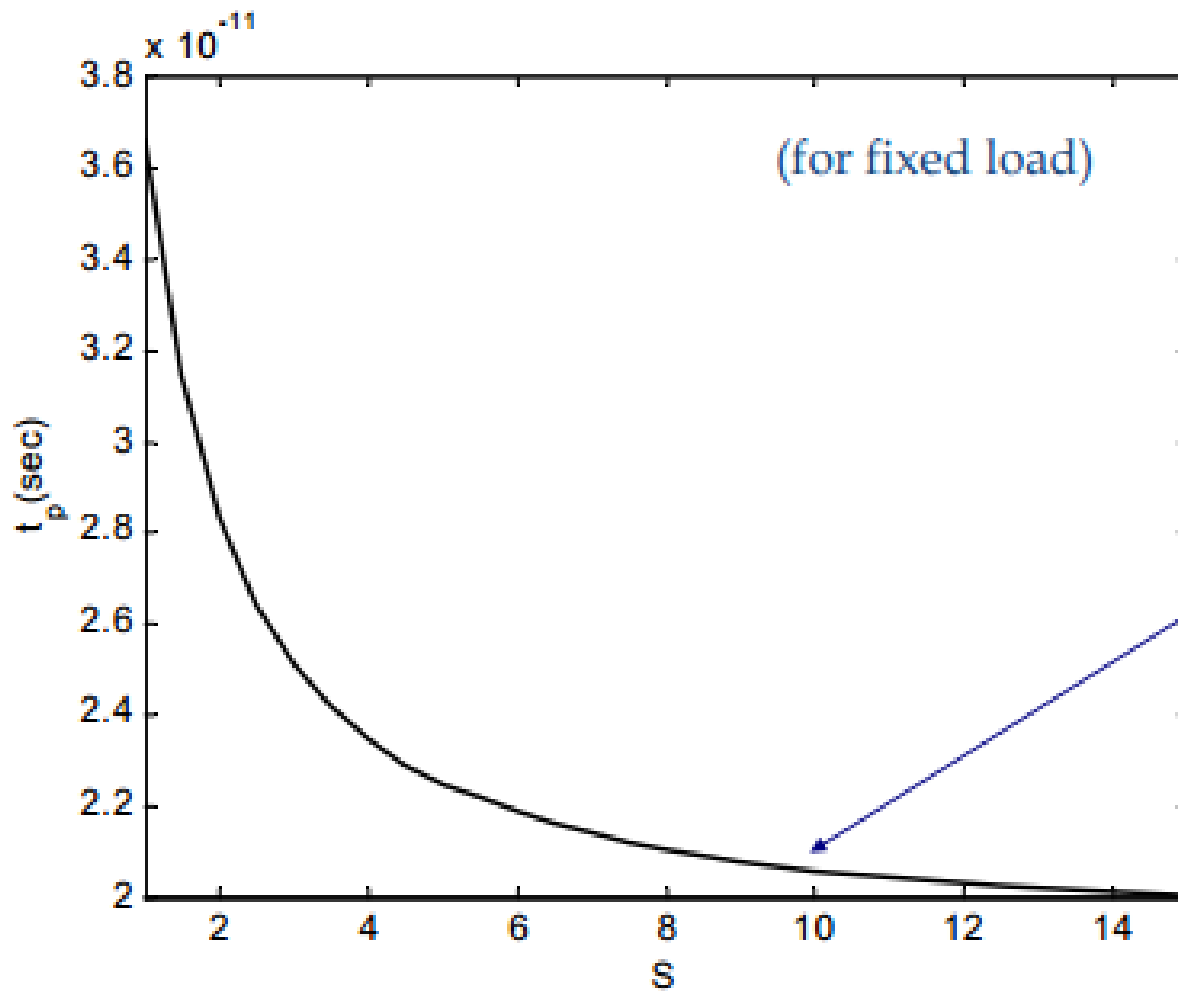


$$V_{out}(t) = (1 - e^{-t/\tau})V$$

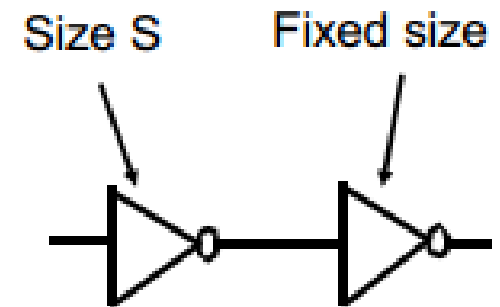
$$\tau = R \times C$$

$$t_p = \ln(2)\tau = 0.69R \times C$$

Device Sizing

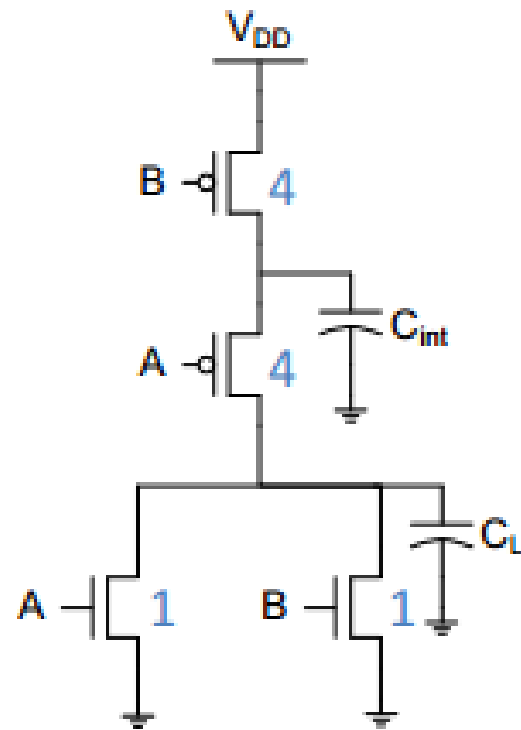
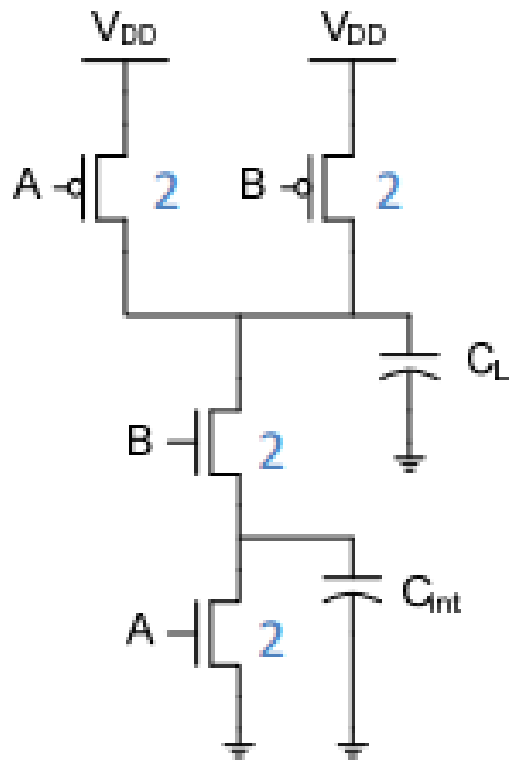


$$S = W_p/W_{p_min} = W_n/W_{n_min}$$

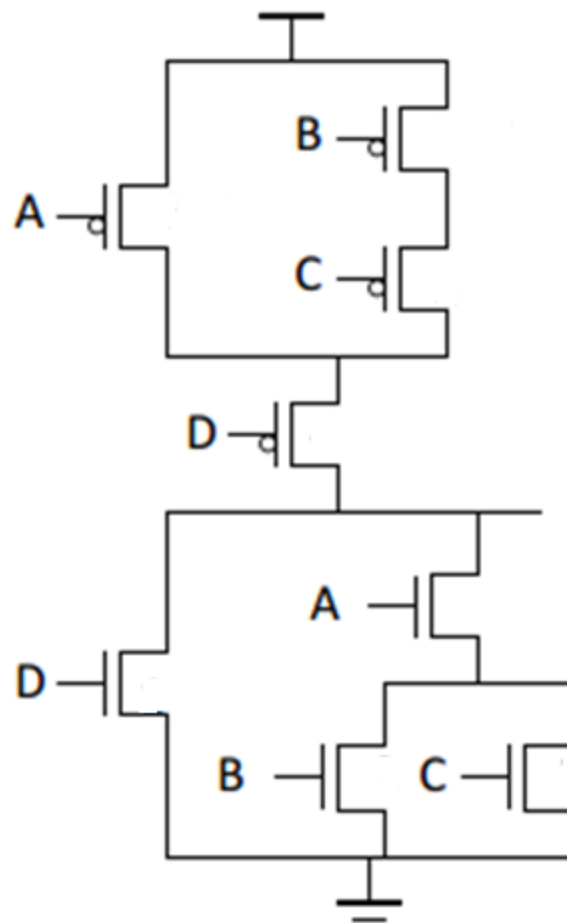


Increasing device width
Leads to self-loading:
Intrinsic capacitances
dominate

Transistor Sizing

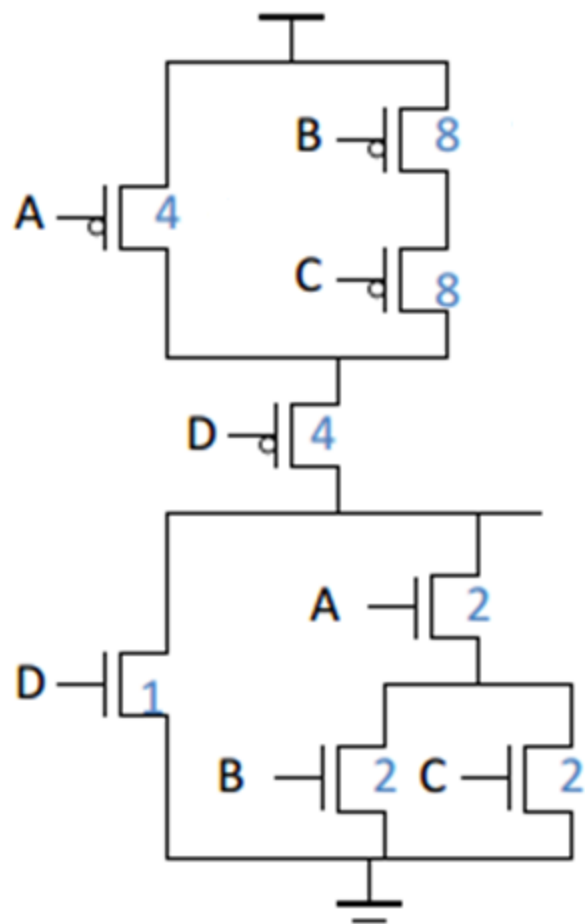


Transistor Sizing a Complex CMOS Gate



$$\text{OUT} = \overline{D + A \cdot (B + C)}$$

Transistor Sizing a Complex CMOS Gate



$$\text{OUT} = D + A \cdot (B + C)$$

Summary

- CMOS delays dictated by device sizing, layout, wires
 - RC model is accurate to first-order
 - Computing delays of complex gates is challenging due to input pattern dependency
 - Watch out for self-loading; size appropriately

Logic Effort

Logical Effort Motivation

- Sizing of a chain of inverters
 - Geometric progression
- How about more complex logic?
- Logical Effort objectives:
 - Quick & dirty, back of the envelope sizing
 - Make trade-off between circuits
 - What is the best circuit topology for a function?
 - How many stages of logic give least delay?
 - How wide should the transistors be?

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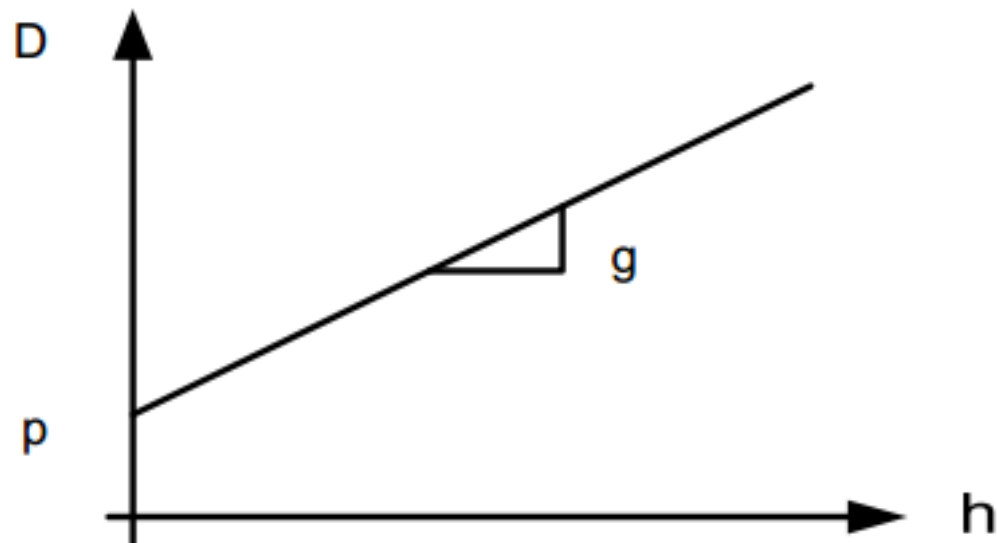
Delay in a Logic Gate

- Express delays in process-independent unit
- Delay has two components:

$$d = f + p$$

- *f*: effort delay = gh (a.k.a. stage effort)
 - Again has two components
- *g*: logical effort
 - Measures relative ability of gate to deliver current
 - $g \equiv 1$ for inverter
- *h*: electrical effort = $C_{\text{out}} / C_{\text{in}}$
 - Ratio of output to input capacitance
 - Sometimes called fanout
- *p*: parasitic delay
 - Represents delay of gate driving no load
 - Set by internal parasitic capacitance

Units of effort



- Reference is the inverter:

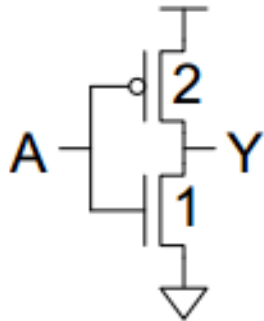
$$g_{inv} = 1$$

$$p_{inv} = 1\tau \quad 20\text{ps of } 250\text{nm}$$

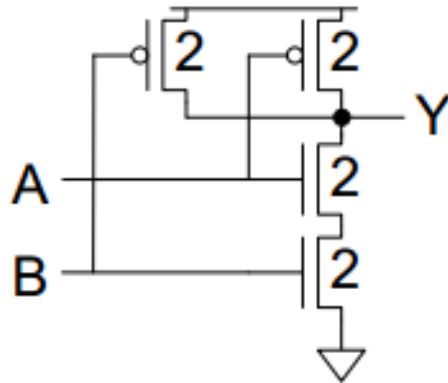
- g is a function of the complexity of a gate, not its size
- p is a function of the technology and gate type

Computing Logical Effort

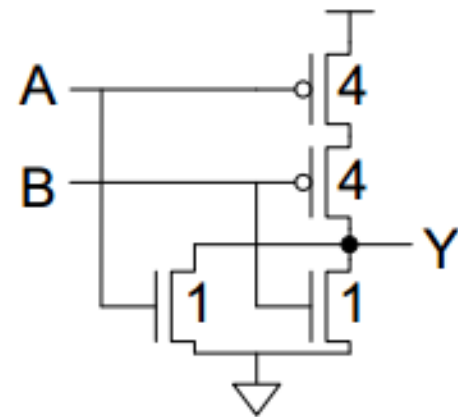
- DEF: *Logical effort is the ratio of the input capacitance of a gate to the input capacitance of an inverter delivering the same output current (i.e, effort delay under same loading).*
- Measure from delay vs. fanout plots
- Or estimate by counting transistor widths



$$C_{in} = 3$$
$$g = 3/3$$



$$C_{in} = 4$$
$$g = 4/3$$



$$C_{in} = 5$$
$$g = 5/3$$

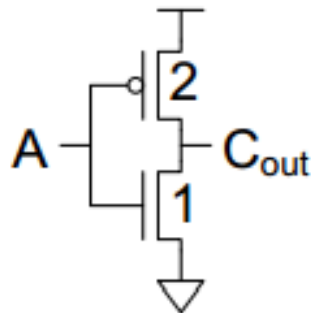
Logical effort (g)

Number of inputs

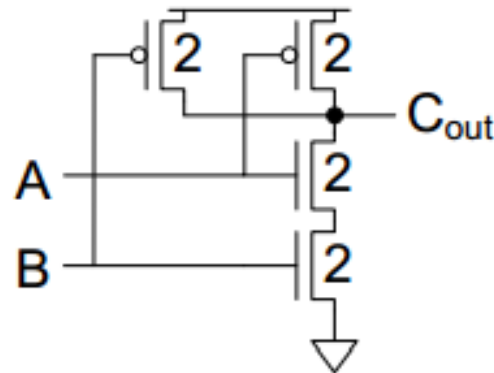
Gate type	1	2	3	4	5	n
Inverter	1					
NAND		$4/3$	$5/3$	$6/3$	$7/3$	$(n + 2)/3$
NOR		$5/3$	$7/3$	$9/3$	$11/3$	$(2n + 1)/3$
Multiplexer		2	2	2	2	2

Computing Parasitic Delay

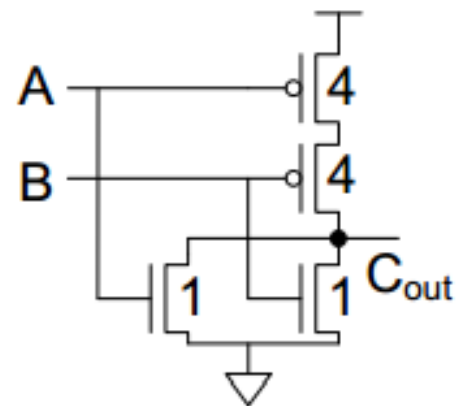
- Measure from delay vs. fanout plots
- Or estimate by counting self loading on output node for sizing with equal output current to inverter
- For simplification, we ignore internal node capacitance



$$C_{out} = 3$$
$$p = 3/3$$



$$C_{out} = 6$$
$$p = 6/3 = 2$$

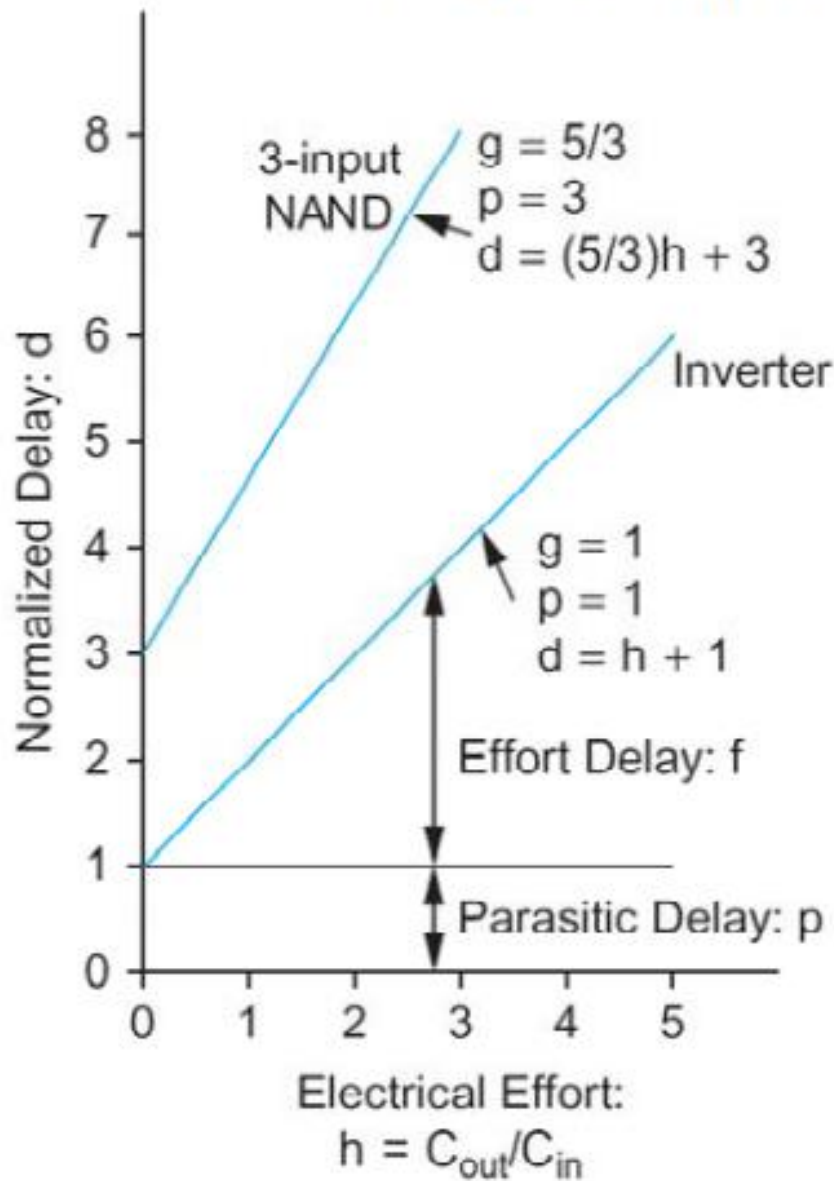


$$C_{out} = 6$$
$$p = 6/3 = 2$$

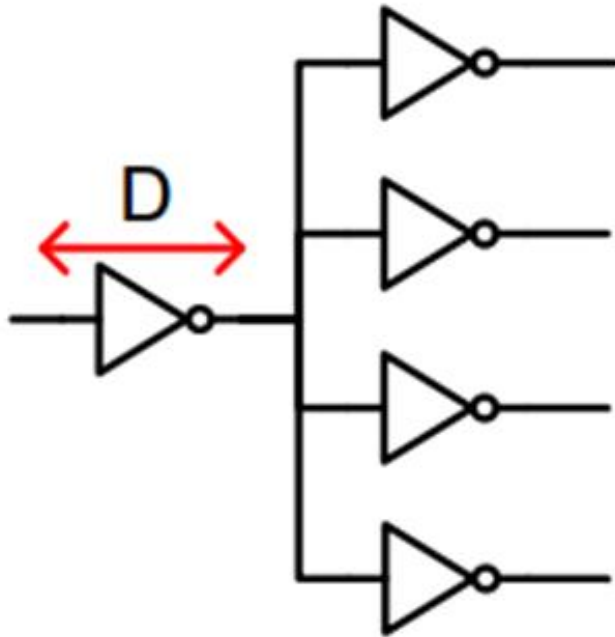
Parasitic Delay (p)

Gate type	Parasitic Delay
Inverter	p_{inv}
n-input NAND	$n \cdot p_{inv}$
n-input NOR	$n \cdot p_{inv}$
n-way multiplexer	$2n \cdot p_{inv}$

Delay components



Fanout 4 Example



$$C_{out} = 4C_{in}$$

$$h = 4$$

$$g = 1$$

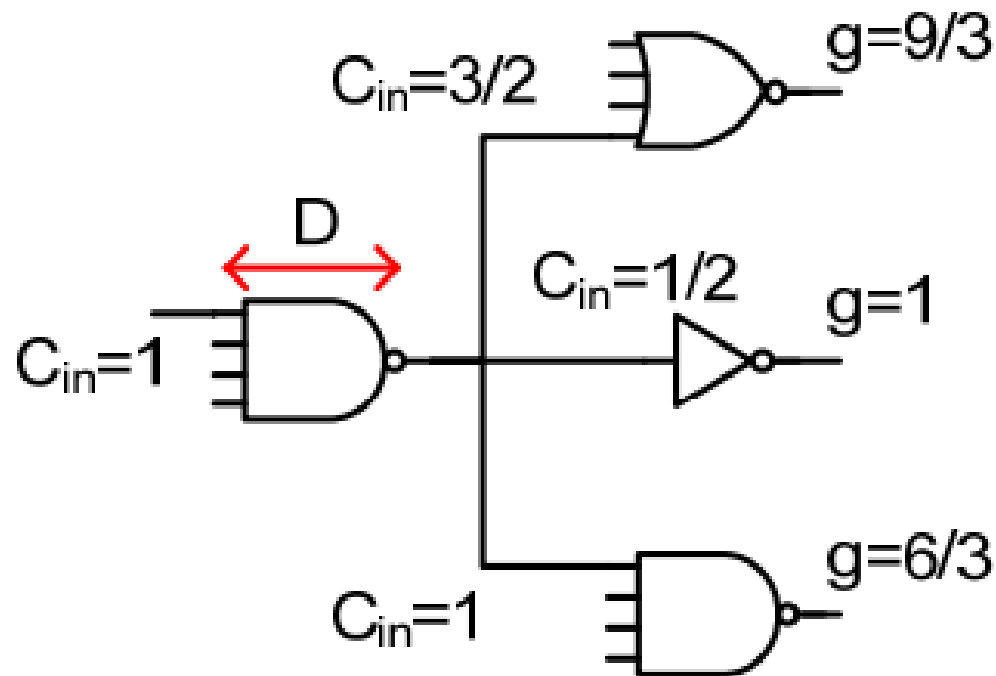
$$p = 1$$

$$D = 4 + 1 = 5\tau$$

FO4 delay

96ps of 250nm

More complex circuit



$$h = 3$$

$$g = \frac{6}{3}$$

$$p = 4 \times 1$$

$$D = 10\tau$$